

## LCP3121

### Application Specific Discretes A.S.D.™

## OVERVOLTAGE AND OVERCURRENT PROTECTION FOR TELECOM LINE

#### **FEATURES AND BENEFITS**

- UNIDIRECTIONAL OVERVOLTAGE PRESSOR PROGRAMMABLE BY VOLTAGE AND CURRENT:
- PROGRAMMABLE BREAKDOWN VOLTAGE UP TO 100 V.
- PROGRAMMABLE CURRENT LIMITATION FROM 120 mA TO 600 mA.
- MULTI-LINE PROTECTION MODE : ONE DE-VICE CAN PROTECT SEVERAL LINES.
- HIGH SURGE CURRENT CAPABILITY:  $I_{PP} = 100A \text{ for } 10/1000 \text{ }\mu\text{s}.$

#### **DESCRIPTION**

Dedicated to the protection of sensitive telecom equipment, the LCP3121 provides protection which can be programmed by both voltage and

The breakdown voltage can be easily programmed by using an external zener diode.

The protection function programmed by the current is achieved with the use of a resistor between the gate and the cathode. The value of the resistor will determine the level of the desired current before the triggering of the device.

A multiple protection mode is also performed when using several diodes providing each line interface with an optimized protection level.

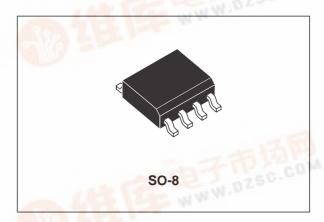
If desired, a bidirectional protection function can be achieved by the use of two LCP3121.

### **COMPLIES WITH THE FOLLOWING STANDARDS:**

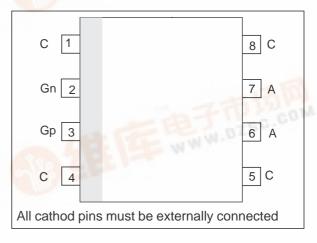
CCITT K20:	10/700μs 5/310μs	6kV 150A
VDE 0433:	10/700μs	2kV 50A
VDE 0878:	5/310μs 1.2/50μs	1.5kV
FCC part 68 :	1/20μs 2/10μs	40A 2.5kV
BELLCORE	2/10μs	200A (*)
TR-NWT-001089:	<mark>2/10</mark> μs 2/10μs	2.5kV 200A (*)
BELLCORE	2/10μ3	2007()

TR-NWT-000974: 10/1000µs 1kV 10/1000µs 100A

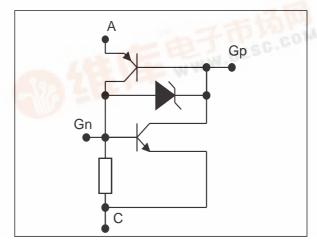
# (\*) with series resistors or PTC.



### **PIN-OUT CONFIGURATION**



### **FUNCTIONAL DIAGRAM**



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## LCP3121

## ABSOLUTE MAXIMUM RATINGS ( T<sub>amb</sub> = 25°C)

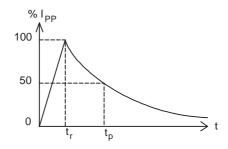
Symbol	Parameter	Value	Unit	
I <sub>PP</sub>	Peak pulse current (see note 1) 10/1000μs		100	Α
I <sub>TSM</sub>	Non repetitive surge peak on-state current $t_p = 10 \text{ms}$ $t = 1 \text{s}$		16 8	А
V <sub>AC</sub> V <sub>GA</sub>	Maximum voltage between A and C Maximum voltage between G (Gn or Gp) and A	100 80	V	
T <sub>stg</sub> T <sub>j</sub>	Storage temperature range Maximum junction temperature		- 40 to + 150 150	°C
TL	Maximum lead temperature for soldering during 10s		260	°C

Note 1 : Pulse waveform :

10/1000μs

t<sub>r</sub>=10μs

tp=1000μs

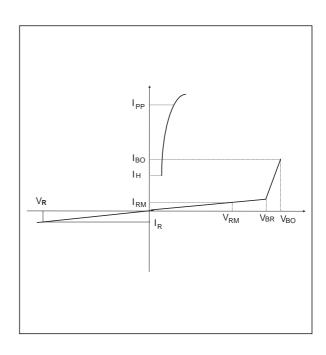


### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R <sub>th (j-a)</sub>	Junction to ambient	170	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>amb</sub> = 25°C)

Symbol	Parameter		
V <sub>RM</sub>	Stand-off voltage		
$V_{BR}$	Breakdown voltage		
V <sub>BO</sub>	Breakover voltage		
lΗ	Holding current		
I <sub>BO</sub>	Breakover current		
I <sub>RM</sub>	Leakage current at V <sub>RM</sub>		
I <sub>R</sub>	Leakage current at V <sub>R</sub>		
I <sub>PP</sub>	Peak pulse current		
V <sub>R</sub>	Continuous reverse voltage		
C <sub>off</sub>	Off-state capacitance		
V <sub>G</sub>	Gate voltage		
$I_{GP}$	Gp triggering current		
I <sub>GN</sub>	Gn triggering current		



## 1 - OPERATION WITHOUT GATE (T<sub>amb</sub> = 25 °C)

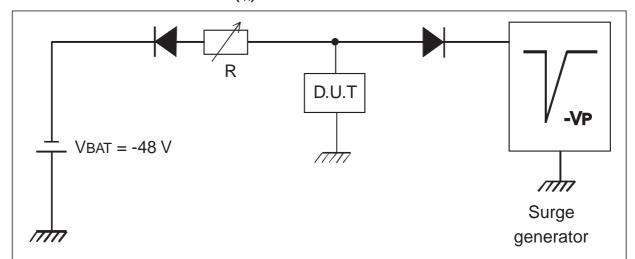
Sym- bol	Test conditions	Min.	Max.	Unit
I <sub>RM</sub>	$V_{RM} = 60V$ $V_{RM} = 90V$		5 8	μА
I <sub>R</sub>	at VR = 180V		50	μА
V <sub>BR</sub>	at 1mA	100		V
I <sub>BO</sub>		80	500	mA
V <sub>BO</sub>	Measured at 50Hz		180	V
lΗ	See the functional test circuit	100		mA

## **2 - OPERATION WITH GATE** $(T_{amb} = 25 \, ^{\circ}C)$

Symbol	Test conditions	Min.	Max.	Unit
V <sub>G</sub>	I <sub>GATE</sub> = 200mA (for eigher Gn or Gp)	0.6	1.8	V
(note1)				
I <sub>GP</sub>	V <sub>Anode-cathode</sub> = 60V		180	mA
I <sub>GN</sub>	V <sub>Anode-cathode</sub> = 60V	80	200	mA

Note 1 :  $V_G = V_{GN}$ , measured between Gn and cathode  $V_G = V_{GP}$ , measured between Gp and anode

### FUNCTIONAL HOLDING CURRENT (IH) TEST CIRCUIT: GO-NO GO TEST



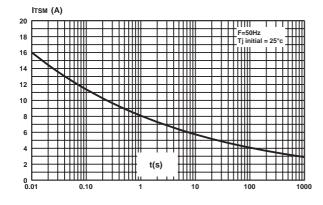
This is a GO-NO GO test which allows to confirm the holding current (I<sub>H</sub>) level in a functional test circuit.

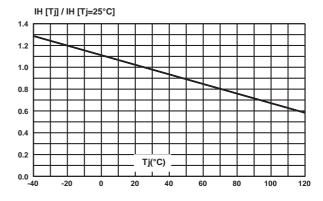
### **TEST PROCEDURE:**

- Adjust the current level at the I<sub>H</sub> value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current :  $I_{PP} = 10A$ ,  $10/1000\mu s$ .
- The D.U.T. will come back to the off-state within a duration of 50ms max.

**Fig. 1:** Maximum non repetitive surge peak-on-state current versus overload duration.

**Fig. 2:** Relative variation of holding current versus junction temperature (typical values).

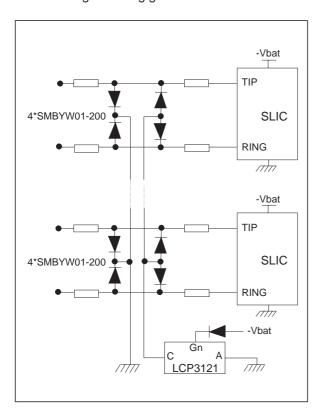




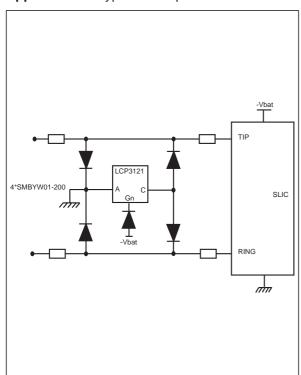
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#### **APPLICATION EXAMPLES**

**Application 1:** Common protection for SLIC without integrated ring generator

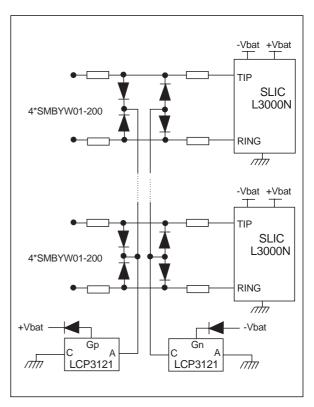


**Application 3:** Typical SLIC protection

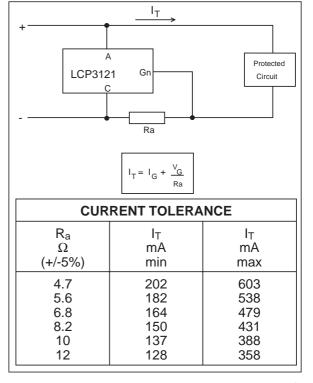


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**Application 2:** Common protection for SLIC with integrated ring generator

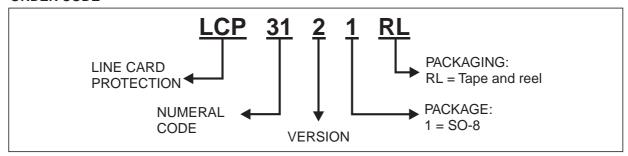


**Application 4:** Protection programmed by current for any application

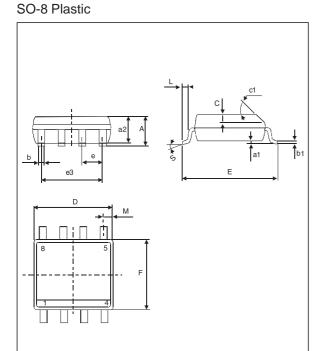


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#### **ORDER CODE**



## PACKAGE MECHANICAL DATA



	DIMENSIONS					
REF.	Millimetres				Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С		0.50			0.020	
с1	45° (typ)					
D	4.8		5.0	0.189		0.197
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
еЗ		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max)					

### **MARKING**

Package	Туре	Marking	
SO-8	LCP3121	CP3121	

**Weight =** 0.08 g

**Packaging:** Products supplied in anti-static tubes or tape and reel.

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